

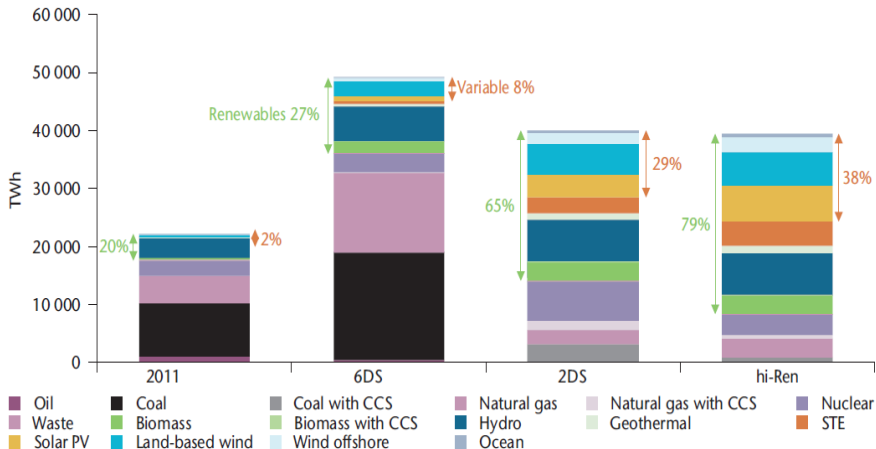


**Weierstrass Institute for
Applied Analysis and Stochastics**



Mathematical opportunities and challenges in sustainable energies

Barbara Wagner

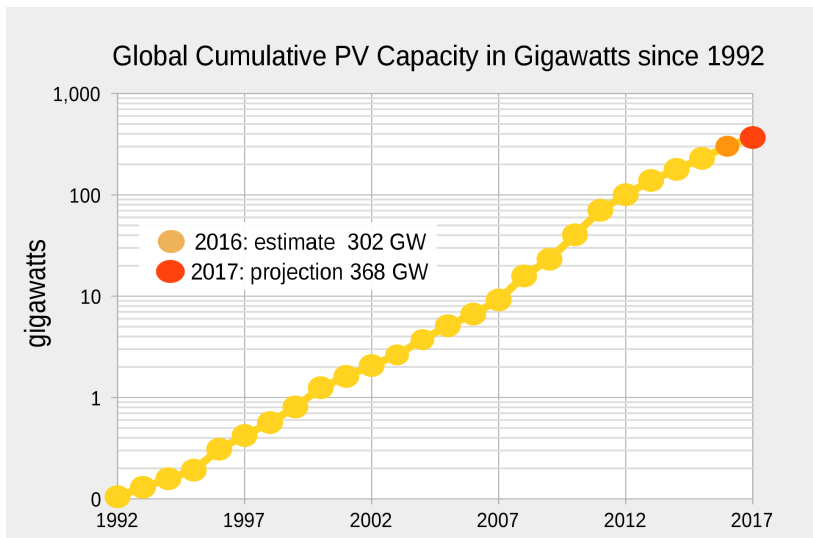


IEA Energy Technology Perspectives 2014b

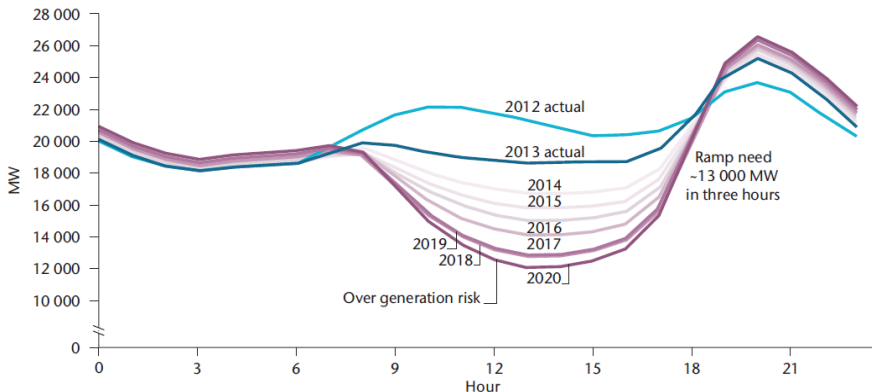
Photovoltaics, Solar Thermal Energy, Concentrated Solar Power, ...



Photo: Harvey Georges/Corbis



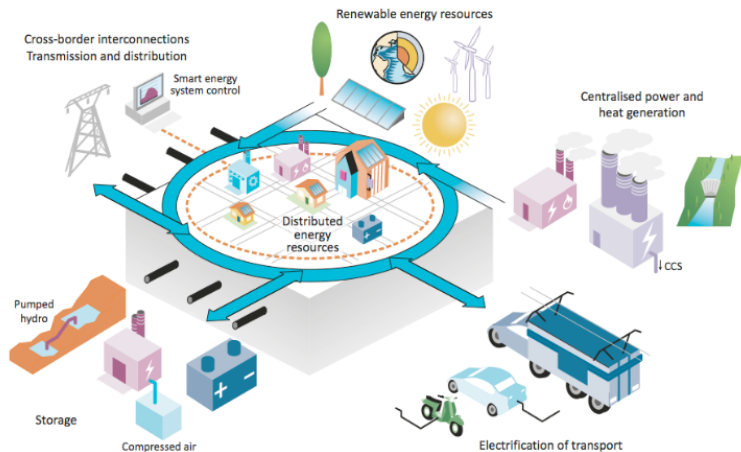
Global Market Outlook for Solar Power 2014, 2015, 2016



Source: California ISO (Independent System Operator) (2013), *What the Duck Chart Tells Us About Managing a Green Grid*, Fast Facts, Folsom, CA, accessed 4 June 2014.

- **Storage:** large-scale stationary battery systems, solar fuels, hydrogen, ...
- **Networks:** prosumers (household solar power systems, electric vehicle batteries, ...)

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Note: CCS = carbon capture and storage.

Source: Reprinted from IEA (2014b), *Energy Technology Perspectives*.

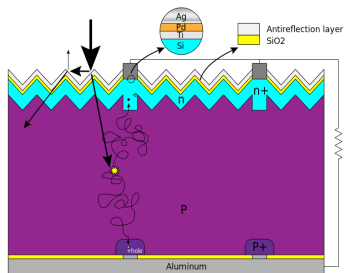
1 Photovoltaics

2 Case studies: Microstructure control

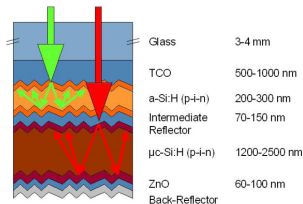
3 Rechargeable batteries

SOLAR CELL

- Basic principle: **pn-junction**
- p-layer and n-layer brought together
 - ⇒ **Depletion layer**
 - ⇒ electric field
- Photon hits silicon atom ⇒ electron excited from valence to conduction band
- electron “sees” DL ⇒ electrode

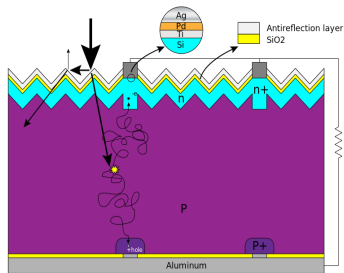


Heart of the solar cell

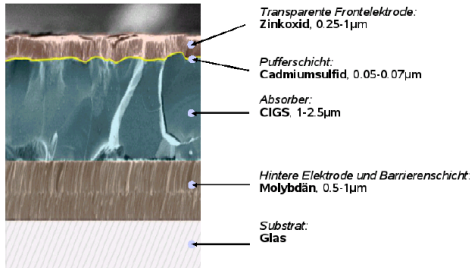


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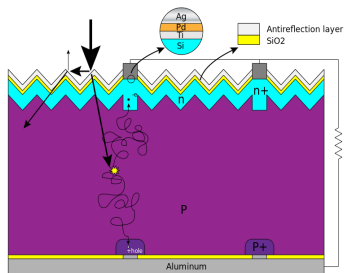


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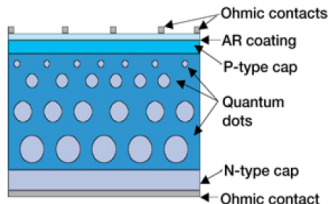


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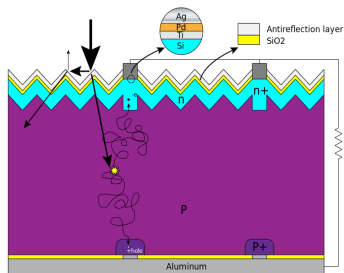
Heart of the solar cell



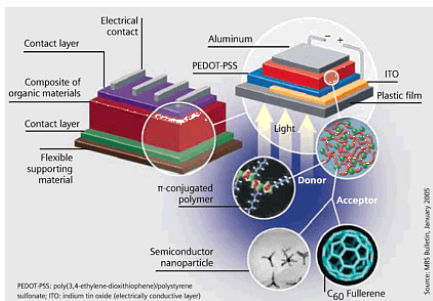
S. M. Shauddin, Energy and Power (2013)

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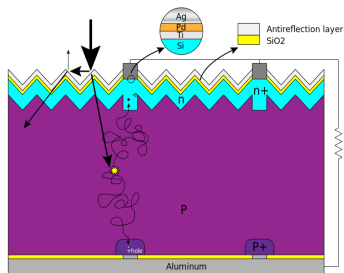


Heart of the solar cell

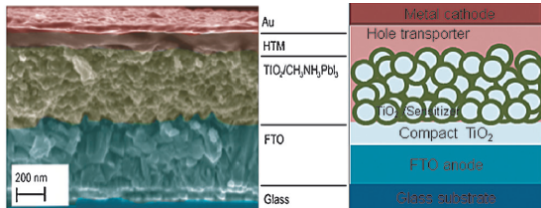


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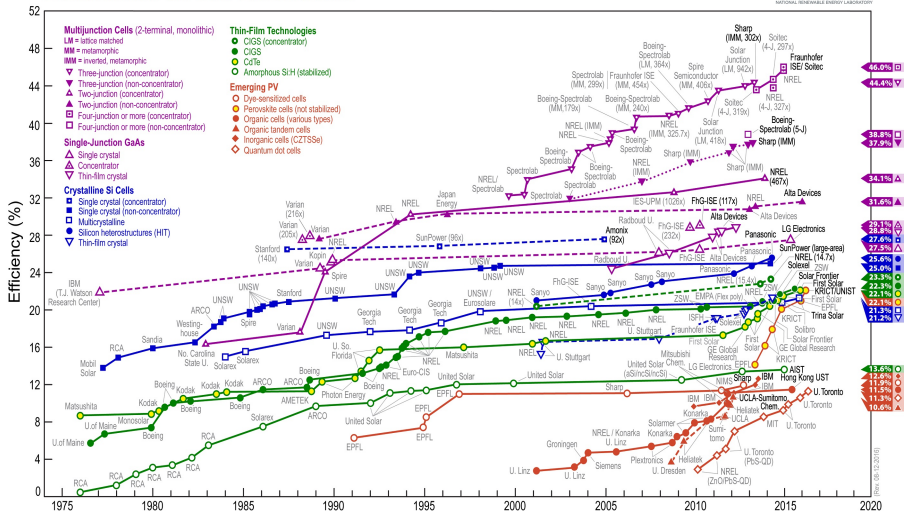


Heart of the solar cell

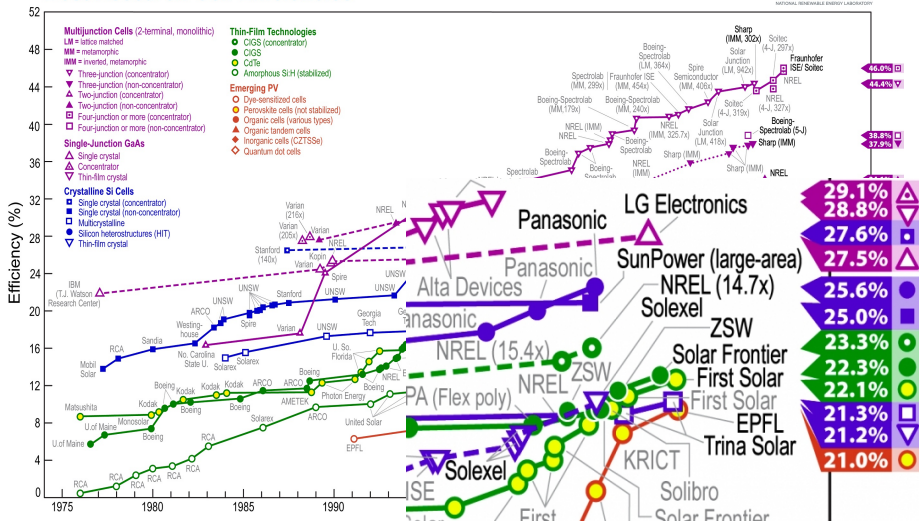


Burschka et al., Nature (2013)

Best Research-Cell Efficiencies



Best Research-Cell Efficiencies



- **2011: Helmholtz-NREL Solar Energy Initiative** collaborate on “...materials and technology that will form the basis of solar cells and solar fuels in the future...”

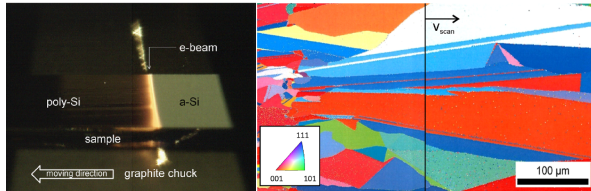


- **Helmholtz Virtual Institute**

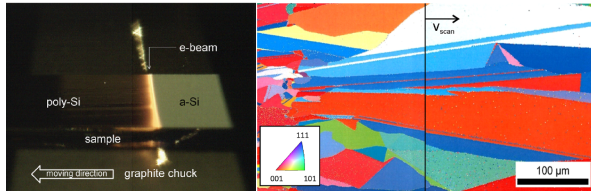
Microstructure control for thin film solar cells

- * **Cu(In,Ga)Se₂ (CIGSe)** absorber layers ⇒ efficiencies > 25 %
- * Multi-junctions, concentrator cells based on CIGSe ⇒ efficiencies > 30 %
- * **Poly-Si** thin films: **cheap production** of high absorber material quality
- * Microstructural features, defects
⇒ electrical & optoelectronic properties of CIGSe & Poly-Si
- * Collaboration: Experimental analyses. modeling on scales from subnanometers to cm, numerical simulations

FOCUS: Line-focussed laser- or e-beam induced liquid-phase crystallization



Becker et al., Sol. Energy Mater. Sol. Cells (2013)



Becker et al., Sol. Energy Mater. Sol. Cells (2013)

- Line-focused electron-beam
- Crystallization exhibit the largest grains & low bulk grain defect density & best electrical material quality
- Cheap large-scale process, **BUT** depends sensitively on the details of grain shapes

Bragard et al., Interf. Sci. (2002), Desai, J. Phys. Chem. Ref. Data (1986), Broughton & Li, Phys. Rev. B (1987), Kobayashi, Physica D (1993), Buta et al., Phys. Rev. E (2007)

Incorporate microscale properties of Si into a phase-field model

Model equation (single 3D grain)

$$\frac{\partial p}{\partial t} = \mathbf{M}(\mathbf{n}, T) \left(\nabla \cdot (\sigma(\mathbf{n})^2 \nabla p) + \sum_{i=1}^3 \partial_{x_i} \left(|\nabla p|^2 \sigma(\mathbf{n}) \frac{\partial \sigma(\mathbf{n})}{\partial (\partial_{x_i} p)} \right) - \frac{\partial F(p, T)}{\partial p} \right)$$

⇒ Determine $\mathbf{M}(\mathbf{n}, T)$ and $\sigma(\mathbf{n})$ with $\mathbf{n} = \frac{\nabla p}{|\nabla p|}$

from expressions for three crystallographic orientations

- $M_{\{100\}}(T), M_{\{110\}}(T), M_{\{111\}}(T)$
- $\varepsilon_{\{100\}}, \varepsilon_{\{110\}}, \varepsilon_{\{111\}}$

Ansatz: 6-fold anisotropy function:

$$\sigma(\mathbf{n}) = \sigma_0 \left(1 + \delta_1 \sum_{i=1}^3 n_i^4 + \delta_2 \prod_{i=1}^3 n_i^2 \right)$$

Determine constants such that:

$$\sigma((1, 0, 0)) = \varepsilon_{\{100\}}, \quad \sigma((1, 1, 0)/\sqrt{2}) = \varepsilon_{\{110\}}, \quad \sigma((1, 1, 1)/\sqrt{3}) = \varepsilon_{\{111\}}$$

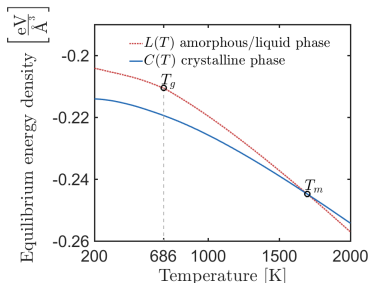
Mobility:
$$\mathbf{M}(\mathbf{n}, T) = \mathbf{M}_0 \left(1 + m_1(T) \sum_{i=1}^3 n_i^4 + m_2(T) \prod_{i=1}^3 n_i^2 \right)$$

with

$$\begin{aligned} \mathbf{M}((1, 0, 0), T) &= M_{\{100\}}(T) \\ \mathbf{M}((1, 1, 0)/\sqrt{2}, T) &= M_{\{110\}}(T) \\ \mathbf{M}((1, 1, 1)/\sqrt{3}, T) &= M_{\{111\}}(T) \end{aligned}$$

$$\frac{\partial p}{\partial t} = M \left[\varepsilon^2 \frac{\partial^2 p}{\partial x^2} - \frac{\partial F}{\partial p}(p, T) \right]$$

- Equilibrium values for the crystalline and liquid phase of Si, at different temperatures¹
- $C(T)$ for the **crystalline** values at $p = 1$ and
- $L(T)$ for the **liquid** values at $p = 0$



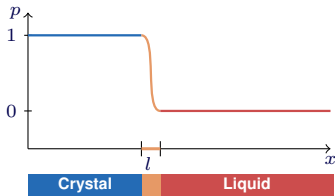
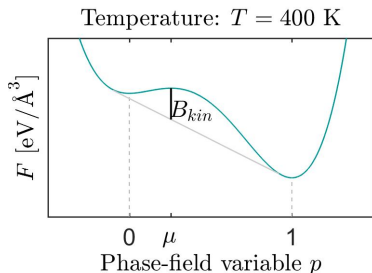
$$F(p, T) = a_0(T) + a_1(T)p + a_2(T)p^2 + a_3(T)p^3 + a_4(T)p^4$$

Fix $a_0(T), \dots, a_4(T)$ s. t. $(\mathbf{0}, \mathbf{F}(\mathbf{0}, \mathbf{T}))$ and $(\mathbf{1}, \mathbf{F}(\mathbf{1}, \mathbf{T}))$
are minima of a double-well potential in p

²Based on MD package by S. Ryu and W.Cai, Stanford Univ.

The **bulk free energy** F is modeled as a double well potential in p .

Coefficient ε of the **gradient energy** depends on the interface thickness l .



$$\varepsilon = l\sqrt{2B_{kin}}, \quad B_{kin} = \gamma/l$$

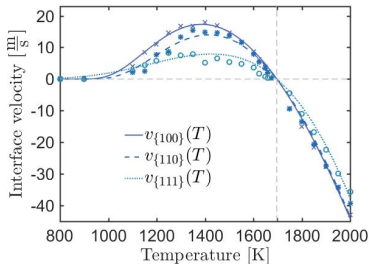
- If we knew **interface energy** $\gamma \Rightarrow$ parameters ε and B_{kin} are specified

Experiments show a **Vogel-Fulcher**-type temperature dependence of interface velocity.²

$$\nu = \text{const} \cdot (T_m - T) \cdot \exp\left(-\frac{B}{T - T_{VF}}\right)$$

Use this in MD simulation using the **Stillinger-Weber potential**.

M is fitted to the MD-calculated velocity and depends on **temperature and orientation**



²S.R. Stiffler, P.V. Evans, A.L. Greer. Acta metall. mater, 40:1617-1622, 1992

$$\frac{\partial p}{\partial t} = M \left[\epsilon^2 \frac{\partial^2 p}{\partial x^2} - \frac{\partial F}{\partial p}(p, T) \right],$$

Have:

$C(T), L(T)$

$v_{\{100\}}(T), v_{\{110\}}(T), v_{\{111\}}(T)$

Find:

$\epsilon_{\{100\}}, \epsilon_{\{110\}}, \epsilon_{\{111\}}$

$F(p, T)$

$M_{\{100\}}(T), M_{\{110\}}(T), M_{\{111\}}(T)$

Need:

$\gamma_{\{100\}}, \gamma_{\{110\}}, \gamma_{\{111\}}$

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$$B_{kin}$$



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Find:

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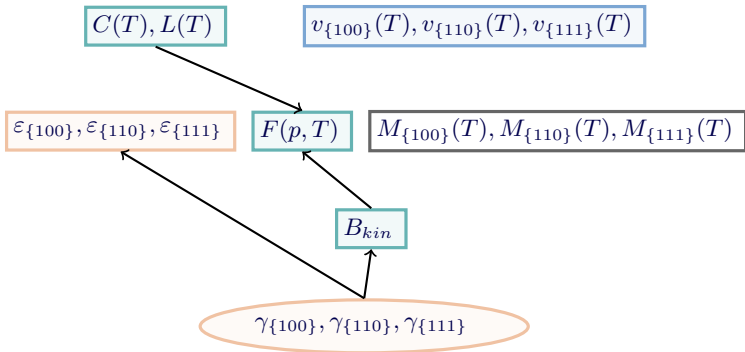
$F(p, T)$

$M_{\{100\}}(T), M_{\{110\}}(T), M_{\{111\}}(T)$

B_{kin}

Need:

$\gamma_{\{100\}}, \gamma_{\{110\}}, \gamma_{\{111\}}$



$$\frac{\partial p}{\partial t} = M \left[\varepsilon^2 \frac{\partial^2 p}{\partial x^2} - \frac{\partial F}{\partial p}(p, T) \right],$$

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$$v_{\{100\}}(T), v_{\{110\}}(T), v_{\{111\}}(T)$$

Find:

$$\varepsilon_{\{100\}}, \varepsilon_{\{110\}}, \varepsilon_{\{111\}}$$

$$F(p, T)$$

$$M_{\{100\}}(T), M_{\{110\}}(T), M_{\{111\}}(T)$$

$$B_{kin}$$

Need:

$$\gamma_{\{100\}}, \gamma_{\{110\}}, \gamma_{\{111\}}$$

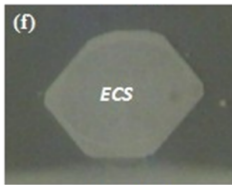
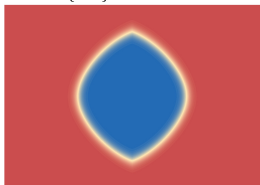
$$\gamma_{\{111\}} < \gamma_{\{110\}} < \gamma_{\{100\}}$$

- $\gamma_{\{100\}} = 0.0262 \text{ eV/\AA}^2$
- $\gamma_{\{110\}} = 0.0218 \text{ eV/\AA}^2$
- $\gamma_{\{111\}} = 0.0212 \text{ eV/\AA}^2$

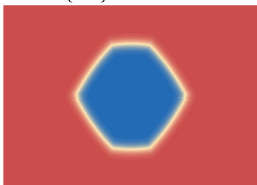
$$\gamma_{\{111\}} < \gamma_{\{100\}} < \gamma_{\{110\}}$$

- $\gamma_{\{100\}} = 0.0234 \text{ eV/\AA}^2$
- $\gamma_{\{110\}} = 0.0277 \text{ eV/\AA}^2$
- $\gamma_{\{111\}} = 0.0212 \text{ eV/\AA}^2$

{110} cut at 44ns

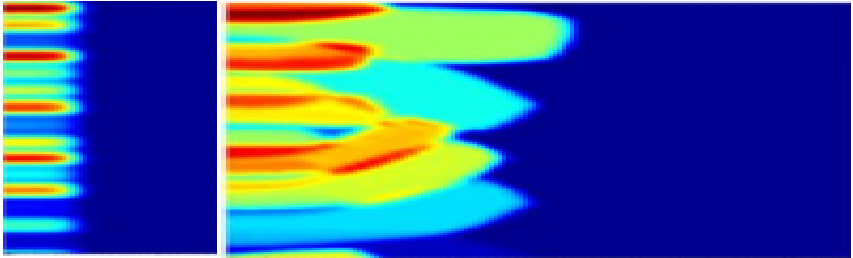


{110} cut at 44ns



Yang et al., Prog.PV.: Res. App. 2014

Apte & Zeng, Appl. Phys. Lett., (2008), Becker & Hoyt, Phys. Rev. E (2007)

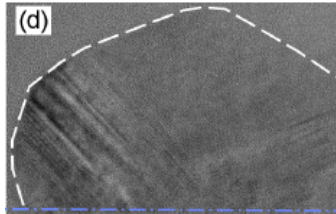
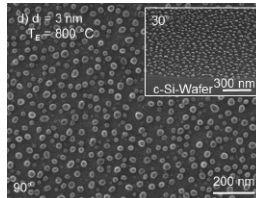
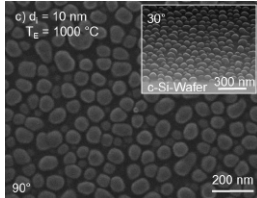
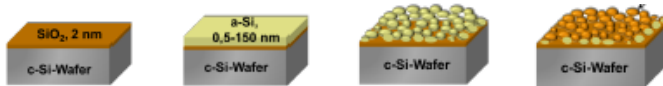



- large scale 3D numerical simulations
- couple to temperature model, defects

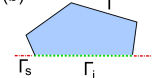
Optimization

- shape of the temperature profile
- scanning speeds
- beam shape

Bergmann, Barragan, Flegel, Albe, W., in: Modelling & Simulation in Mat. Sci. Eng. (2017), Korzec & Wu, DCDS-B (2014)

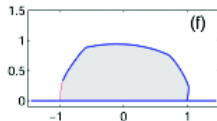
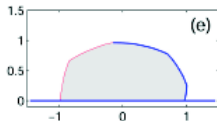
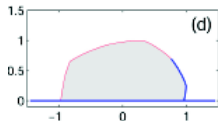


(a)  Γ

(b)  Γ
 Γ_s Γ_i

$$\min_{\Omega} \int_{\Gamma} \gamma dS + \int_{\Gamma_i} \gamma_i dS + \int_{\Gamma_s} \gamma_s dS \quad \text{s.t.} \quad |\Omega| = \text{const.}$$

$$\Rightarrow \min_{x \in \mathbb{R}^N} f(x) \quad \text{s.t.} \quad c(x) = 0, \quad \text{for } x \geq 0$$



Korzec, Roczen, Schade, W., Rech, J. Appl. Phys. (2014), Winterbottom, Acta Metall. (1967), Eaglesham, PRL (1993)

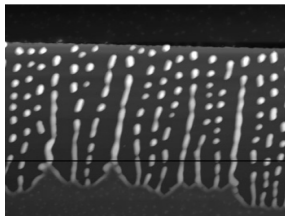
Sharp-interface model

$$V_n = \frac{\partial^2 \mu}{\partial s^2} = \frac{\partial^2}{\partial s^2} [\gamma(\theta) + \gamma''(\theta)] \kappa$$

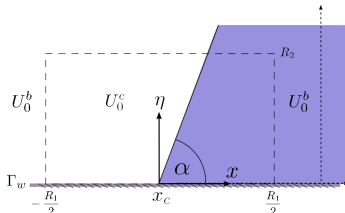
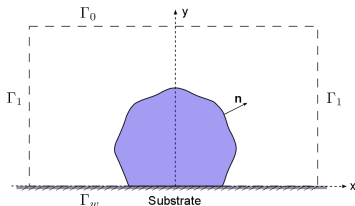
At x_c :

No flux $0 = \frac{\partial}{\partial s} [\gamma(\theta) + \gamma''(\theta)] \kappa$

Young-Herring $\gamma(\theta) \cos \alpha - \gamma'(\theta) \sin \alpha = \frac{\sigma_{FS} - \sigma_{VS}}{\lambda_m}$



Leroy et al. Phys.Rev.B (2012)



Cahn & Taylor, Acta Metall. Mater. (1994), Thompson, Annu. Rev. Mater. Res. (2012), Danielson et al. J. App. Phys. (2006), Pierre-Louis et al., Eur. Phys J. (2010), Wang et al., Phys. Rev. B (2014), Leroy et al., Surf. Sci. Rep. (2016)

Free Energy $W = \int_{\Omega} f_{FV} d\Omega + \int_{\Gamma_w} f_w d\Gamma$

$$f_{FV} = \lambda_m \left(F(u) + \frac{\varepsilon^2}{2} |\nabla u|^2 \right) \quad f_w = \frac{\sigma_{VS} + \sigma_{FS}}{2} - \frac{u(3 - u^2)}{4} (\sigma_{VS} - \sigma_{FS}).$$

Phase-field $\varepsilon^2 \partial_{\tau} u = \nabla \cdot m(u) \nabla \mu \quad \mu = F'(u) - \varepsilon^2 \nabla \cdot \left(\gamma \gamma' \begin{pmatrix} -u_y \\ u_x \end{pmatrix} + \gamma^2 \nabla u \right)$

Boundary conditions

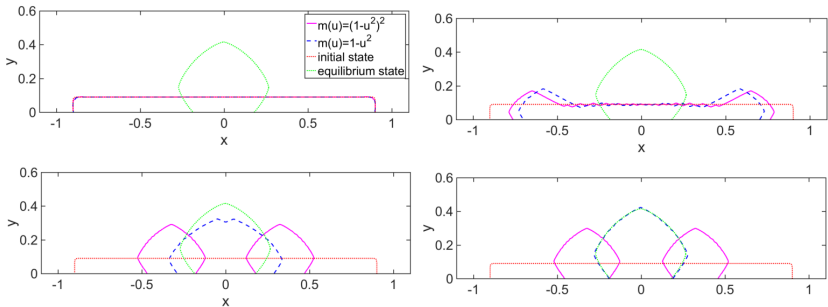
On Γ_w : $\mathbf{n}_{\Omega} \cdot (m(u) \nabla \mu) = 0 \quad \varepsilon \mathbf{n}_{\Omega} \cdot \left[\gamma(\theta) \gamma'(\theta) \begin{pmatrix} -u_y \\ u_x \end{pmatrix} + \gamma(\theta)^2 \nabla u \right] + \frac{f'_w}{\lambda_m} = 0$

On $\Gamma_0 \cup \Gamma_1$: $\mathbf{n}_{\Omega} \cdot (m(u) \nabla \mu) = 0 \quad \mathbf{n}_{\Omega} \cdot \nabla u = 0$

With $F(u) = \frac{1}{2}(1 - u^2)^2$ and $\mathbf{m}(\mathbf{u}) = (1 - \mathbf{u}^2)^2$

Anisotropic phase-field model for solid dewetting

- * Matched asymptotics yields a sharp interface model governed by surface diffusion
- * Matching involves **two interior layers** \Rightarrow and **exponential asymptotics**
- * Dynamics of **triple-points** uses multiple inner layers to obtain the **Young-Herring condition** and the **contact angle**



Phase field model: **Isotropic case** $u \in [1, -1]$

$$u_t = \nabla \cdot [(1 - u^2)^2 \nabla \mu], \quad \mu = -\varepsilon^2 \nabla^2 u + f'(u),$$

$$f(u) = (1 - u^2)^2$$

Sharp interface limit: $\varepsilon \rightarrow 0$ $v_n = \Delta_\Gamma \kappa$

Thin film approximation: $h_t + \Delta^2 h = 0$,

A note on the instability: $n < 3$

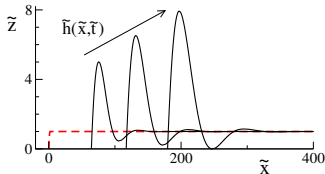
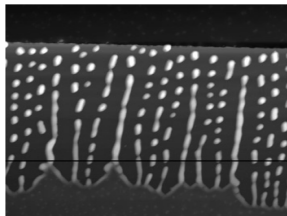
$$h_t + \nabla \cdot (h^n \nabla \Delta h) = 0$$

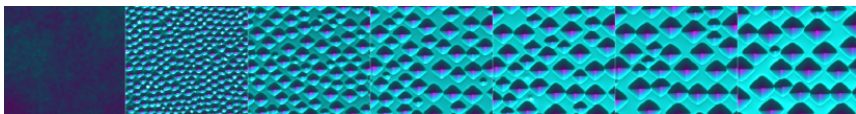
$$h \rightarrow 1 \quad \text{for } x \rightarrow \infty$$

$$h = 0, \quad \nabla h \cdot n_s = 1, \quad h^n (\nabla \Delta h) \cdot n_s = 0 \quad \text{at } x = s(y, t)$$

Three scenarios for the base states

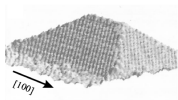
- $n = 0$ finite time rupture
- $3/2 < n < 3$ no finite time rupture
- $0 < n < 3/2$ unknown





Stranski-Krastanov growth

Mullins' surface diffusion formula



$$h_t = \sqrt{1 + |\nabla h|^2} \mathcal{D} \nabla_s^2 \mu$$

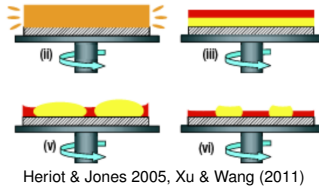
$$\mathcal{F} = \mathcal{F}_{sed} + \mathcal{F}_\kappa + \mathcal{F}_{wet} + \mathcal{F}_{anis} + f$$

C. Teichert et al., Appl. Phys. A (1998)

$$\alpha = \frac{H}{L} \ll \mathbf{O}(1)$$

6th (- 4th) - Order Convective Cahn-Hilliard equations

Asaro, Tiller, Metall. Trans (1972), Grinfeld, Sov. Phys. Dokl. (1987), Spencer, Voorhees, Davis, J Appl Phys (1993), Tersoff et al., PRL (2002), Golovin et al., Phys. Rev. B (2004), Korzec, Evans, Münch, W., SIAM J. Appl. Math. (2008), Khenner, Tekalgin, Levine EPL (2011), Korzec, Nayar, Rybka, J. Dyn. Diff. Equ. (2016)



Donor and acceptor polymers with defined grade of demixing

⇒ Self-organization during layer evaporation

Heterojunction polymer cell: photons generates **excitons**

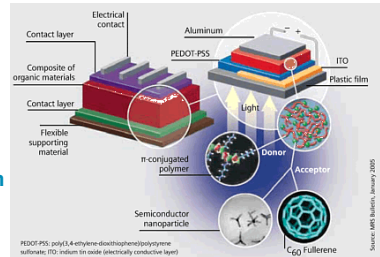
Solar cell performance

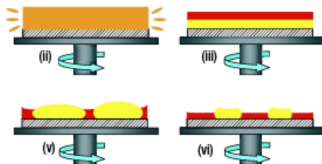
- * Exciton and charge transport in bulk
- * Exciton dissociation at donor-acceptor interface

Exciton and charge carrier **diffusion length of few 10nm**

⇒ optimize the absorber morphology

⇒ **highly folded heterojunction**
with controlled morphology





Heriot & Jones 2005, Xu & Wang (2011)

Donor and acceptor polymers with defined grade of demixing

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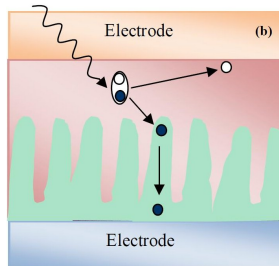
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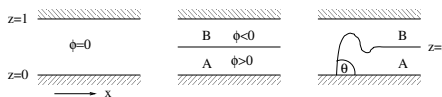
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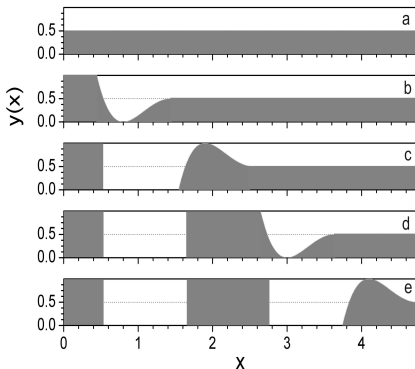
with controlled morphology



Transitions in morphology:



Surface directed spinodal decomposition



ϕ order parameter, μ chemical potential,

F bulk free energy

$$\phi_t = \Delta\mu, \quad \mu = F'(\phi) - \varepsilon^2 \Delta\phi,$$

$$F(\phi) = -\phi^2/2 + \phi^4/4,$$

Assume antisymmetric walls at $z = 0, 1$:

$$\mu_z = 0 \quad (\text{no-flux}),$$

$$\varepsilon\phi_z = \beta_1(1 - \phi^2)$$

Jaczewska et al., Macromolecules (2008), Dunbar et al., Phys. J. E Soft Matter (2010), Buxton and Clarke, Europhys. Lett. (2007), Wodo et al., Appl. Phys. Lett. (2014)

Sharp-interface model

$$\begin{aligned} \Delta \mu_1 &= 0 && \text{for } 0 < z < 1, z \neq h, \\ \partial_z \mu_1 &= 0 && \text{at } z = 0, 1, \\ \mu_1 &= \sigma \kappa && \text{at } z = h, \\ h_t &= - \frac{\nabla \mu_1 \cdot (-h_x, 1)}{2} \Big|_{-}^{+} && \text{at } z = h, \end{aligned}$$

At the 3-phase contact-line:

$$h = 0, \quad h_x = \tan \theta, \quad q = \partial_x \int_0^1 \mu dz = 0$$

with $\cos \theta = \frac{2\beta_1}{3\sigma}$ (Cahn 77 - Modica 87)

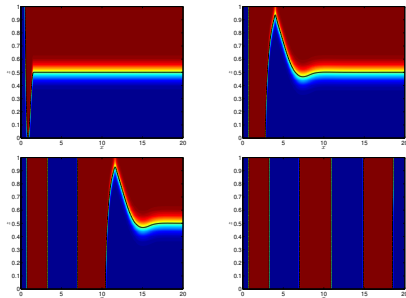
At $x \rightarrow \infty$: $h \rightarrow 1, \quad q \rightarrow 0$

Thin film approximation

$$h_t + h_{xxxx} = 0, \quad (n = 0)$$

$$x = s(t) : h = 0, \quad h_x = 1, \quad h_{xxx} = 0;$$

$$x \rightarrow \infty : h \rightarrow 1, \quad h_{xxx} \rightarrow 0.$$



No/weak surface energy: $\theta = 85^\circ, \varepsilon = 0.03,$
 $\beta_1 = 0.03$. Solution shown at times $t = 0,$
 $t = 165, t = 498$ and final state

Puri & Binder (2007), Gheoghegan & Krausch
 (2003), Xu & Wang 2011, Hennessey et al.
 2014, 2015

- Rechargeable batteries, hydroelectric power, solarfuels

Rechargeable batteries, hydroelectric power, solarfuels

LITHIUM ION BATTERIES

Phyisco-chemical phenomena

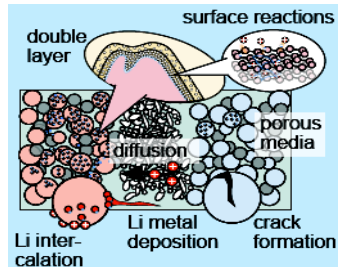
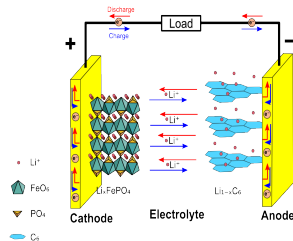
- Ion diffusion in electrolytes
- Lithium intercalation of electrodes
- Surface and transfer reactions
- Electrochemical double layers
- Many particle electrodes

Battery management

- Assessment of State of Health (SOH)
- ageing of battery

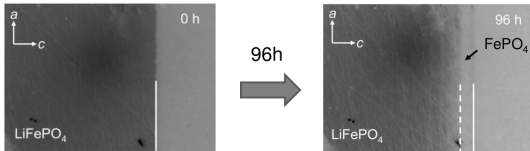
Further problems

- Online assessment of SOH: faster than real time simulations for e-vehicles
- **2nd life batteries:** Recycle automobile batteries for large scale stationary storage systems



Phase Transition in LiFePO_4

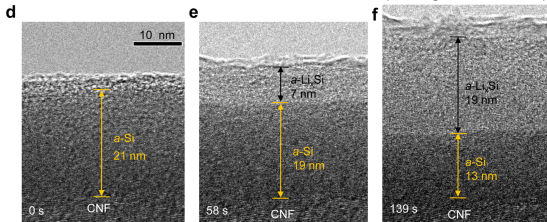
(Weichert et al. 2012)



- LiFePO_4 undergoes a phase transition. Changes in volume 6.8%.

2-Phase Lithiation in a-Si

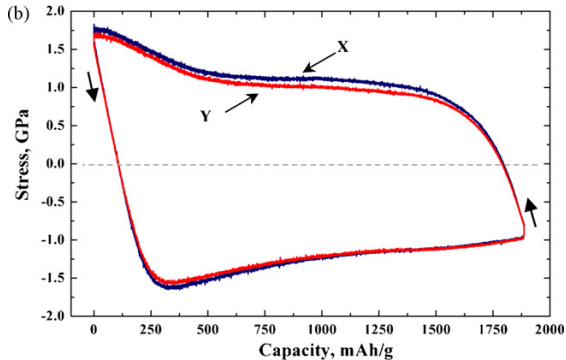
(Wang et al. 2013)



- c-Si and a-Si undergo two-phase lithiation. Si changes in volume 300%. Si has a huge specific charge, 4200 mAhg^{-1} compared to graphite, 372 mAhg^{-1}

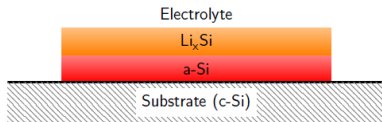
Cogswell, Bazant, Nano (2012), Cubuk, Kaxiras, Nano Lett (2014), Levitas et al., J. Mech. Phys. Solids (2016),

Stress curve for a thin layer electrode (Sethuraman et al 2010):



- Zhao et al. (2012), Pharr et al. (2014) based on yield stress.
The yield stress does not reach the theoretical value.
- **What would the effect of a phase transition be?**

Simplified experimental set-up



$$c_t = \nabla \cdot (M(c)\nabla\mu)$$

$$\mu = -\Delta c + W_c^{\text{ch}}(c) + W_c^{\text{el}}(e(u), c) + \nu c_t$$

$$0 = \text{div}(W_e^{\text{el}}(e(u), c))$$

- * c vector of concentrations, u displacement field
- * The elastic energy W^{el} will in general be nonlinear, anisotropic
- * $M(c)$ mobility matrix, in general anisotropic.
- * νc_t is the viscous term, ν could depend on c too.
- * Y reaction term, general nonlinear function $R(c, \mu)$

Boundary conditions

Electrolyte

$$\sigma \cdot n = 0$$

$$n \cdot \nabla c = 0$$

$$n \cdot \nabla \mu = Y.$$

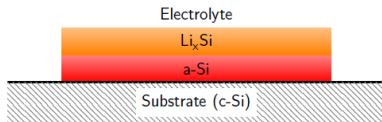
Substrate

$$u = 0$$

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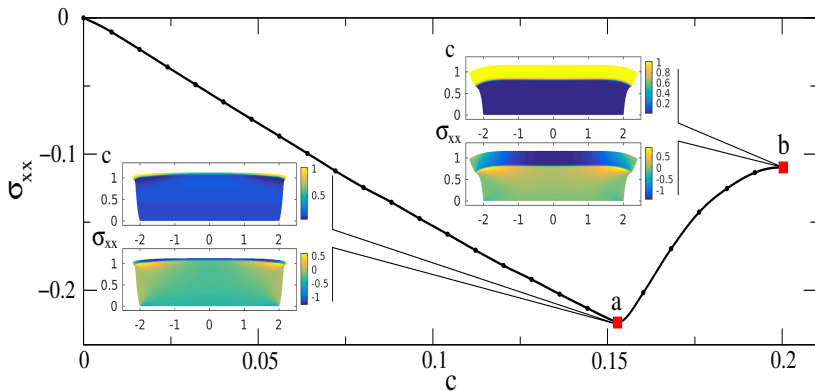
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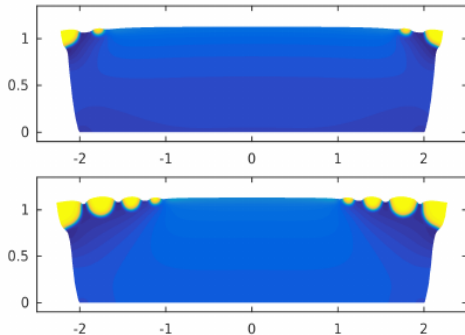
$$n \cdot \nabla c = 0$$

$$n \cdot \nabla \mu = 0.$$

- * Assume constant flux boundary conditions, isotropic mobility and elasticity, concentration dependent elastic constants and eigenstrain
- * Numerical method: finite volume with an adaptive nonlinear multigrid algorithm (S. Wise et al 2007).



Sethuraman et al. (2010), Meca, Münch, W., PRS A (2016), EJAM (2017)



Meca, Münch, W., WIAS preprint 2387 (2017), Kraus, Roggensack, WIAS preprint 2231 (2016)

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Esteban Meca (WIAS)

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Virtual Institute: Microstructure
control for thin film solar cells

